



ON Semiconductor®

# FDD2670

## 200V N-Channel PowerTrench® MOSFET

### General Description

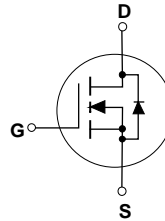
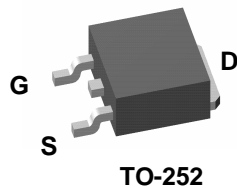
This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers.

These MOSFET's feature faster switching and lower gate charge than other MOSFET's with comparable  $R_{DS(ON)}$  specifications.

The result is a MOSFET that is easy and safer to drive (even at very high frequencies), and DC/DC power supply designs with higher overall efficiency.

### Features

- 3.6 A, 200 V.  $R_{DS(ON)} = 130 \text{ m}\Omega @ V_{GS} = 10 \text{ V}$
- Low gate charge
- Fast switching speed
- High performance trench technology for extremely low  $R_{DS(ON)}$
- High power and current handling capability



### Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{DSS}$	Drain-Source Voltage	200	V
$V_{GSS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current – Continuous (Note 1)	3.6	A
	Drain Current – Pulsed	20	
$P_D$	Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$ (Note 1)	70	W
	@ $T_A = 25^\circ\text{C}$ (Note 1a)	3.2	
	@ $T_A = 25^\circ\text{C}$ (Note 1b)	1.3	
dv/dt	Peak Diode Recovery dv/dt (Note 3)	3.2	V/ns
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

### Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	1.8	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1b)	96	$^\circ\text{C/W}$

### Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDD2670	FDD2670	13"	16mm	2500 units

## Electrical Characteristics

$T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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### Drain-Source Avalanche Ratings (Note 1)

$W_{DSS}$	Single Pulse Drain-Source Avalanche Energy	$V_{DD} = 100\text{ V}, I_D = 3.6\text{ A}$			375	mJ
$I_{AR}$	Maximum Drain-Source Avalanche Current				3.6	A

### Off Characteristics

$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	200			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$		214		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 160\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
$I_{GSSF}$	Gate-Body Leakage, Forward	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$			100	NA
$I_{GSSR}$	Gate-Body Leakage, Reverse	$V_{GS} = -20\text{ V}, V_{DS} = 0\text{ V}$			-100	NA

### On Characteristics (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2	4	4.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$		-10		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 3.6\text{ A}$ $V_{GS} = 10\text{ V}, I_D = 3.6\text{ A}, T_J = 125^\circ\text{C}$		100 205	130 275	m $\Omega$
$I_{D(on)}$	On-State Drain Current	$V_{GS} = 10\text{ V}, V_{DS} = 5\text{ V}$	20			A
$g_{FS}$	Forward Transconductance	$V_{DS} = 5\text{ V}, I_D = 3.6\text{ A}$		15		S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}$		1228		PF
$C_{oss}$	Output Capacitance	$f = 1.0\text{ MHz}$		112		PF
$C_{riss}$	Reverse Transfer Capacitance			17		pF

### Switching Characteristics (Note 2)

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 100\text{ V}, I_D = 1\text{ A}$		13	23	ns
$t_r$	Turn-On Rise Time	$V_{GS} = 10\text{ V}, R_{GEN} = 6\ \Omega$		8	16	ns
$t_{d(off)}$	Turn-Off Delay Time			30	48	ns
$t_f$	Turn-Off Fall Time			25	40	ns
$Q_g$	Total Gate Charge	$V_{DS} = 100\text{ V}, I_D = 3.6\text{ A}$		27	43	nC
$Q_{gs}$	Gate-Source Charge	$V_{GS} = 10\text{ V}$		7		nC
$Q_{gd}$	Gate-Drain Charge			10		nC

### Drain-Source Diode Characteristics and Maximum Ratings

$I_S$	Maximum Continuous Drain-Source Diode Forward Current				2.1	A
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 2.1\text{ A}$ (Note 2)		0.7	1.2	V

#### Notes:

- $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



a)  $R_{\theta JA} = 40^\circ\text{C/W}$  when mounted on a  $1\text{in}^2$  pad of 2oz copper.



b)  $R_{\theta JA} = 96^\circ\text{C/W}$  on a minimum mounting pad.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width < 300 $\mu\text{s}$ , Duty Cycle < 2.0%

3.  $I_{SD} \leq 3\text{ A}$ ,  $di/dt \leq 100\text{ A}/\mu\text{s}$ ,  $V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$

Typical Characteristics

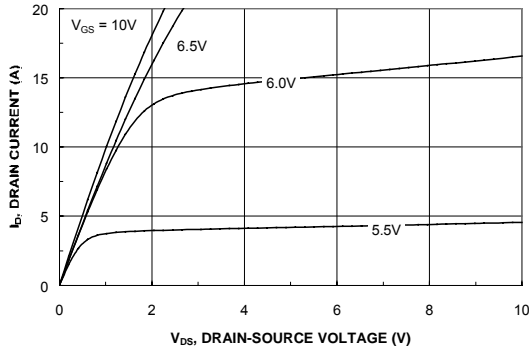


Figure 1. On-Region Characteristics.

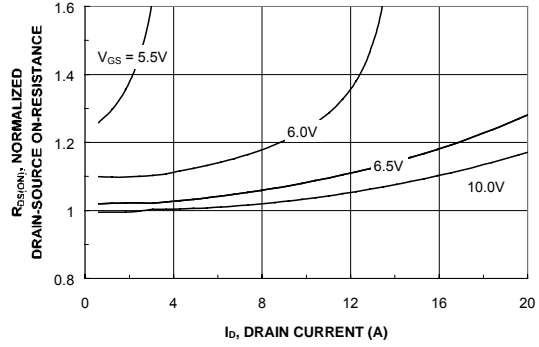


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

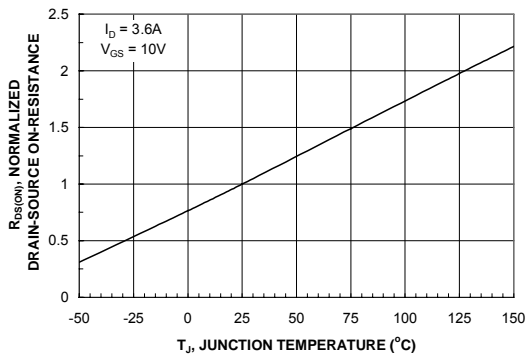


Figure 3. On-Resistance Variation with Temperature.

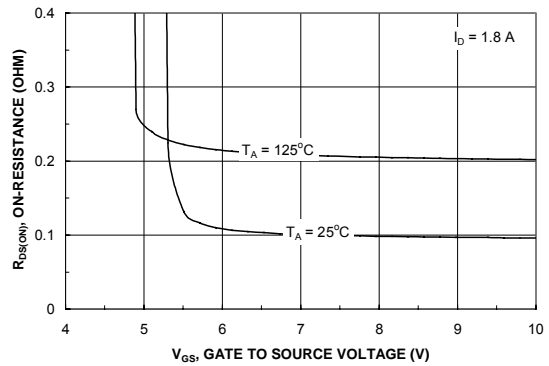


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

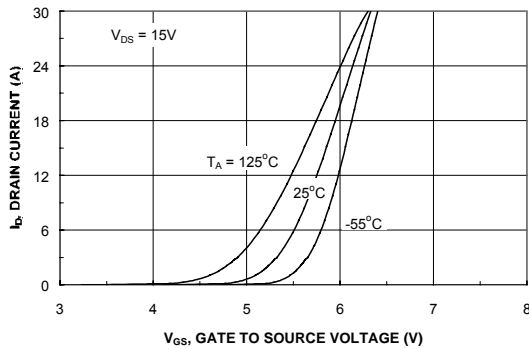


Figure 5. Transfer Characteristics.

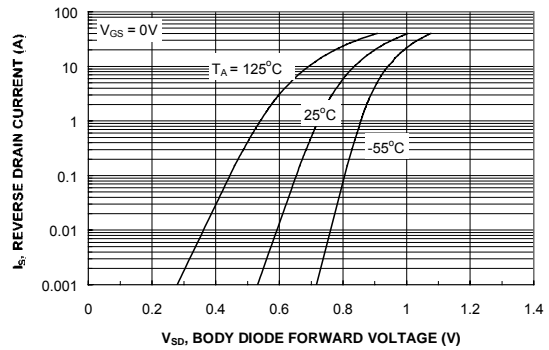


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics

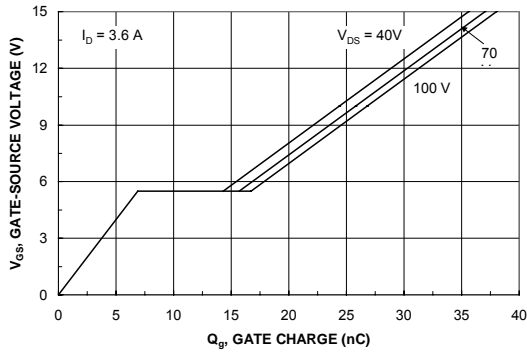


Figure 7. Gate Charge Characteristics.

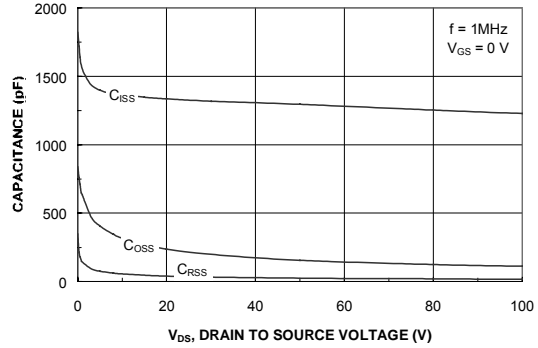


Figure 8. Capacitance Characteristics.

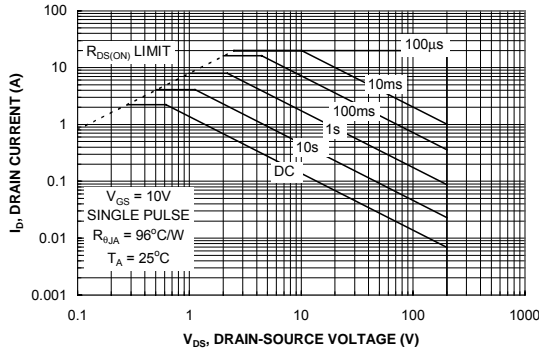


Figure 9. Maximum Safe Operating Area.

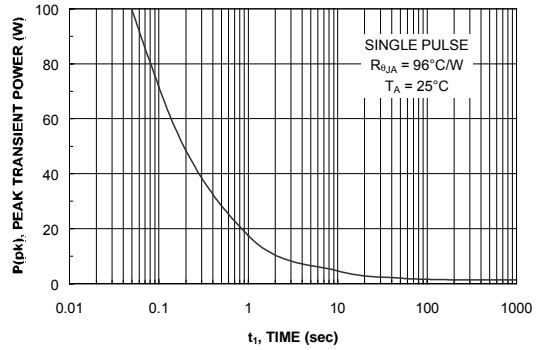


Figure 10. Single Pulse Maximum Power Dissipation.

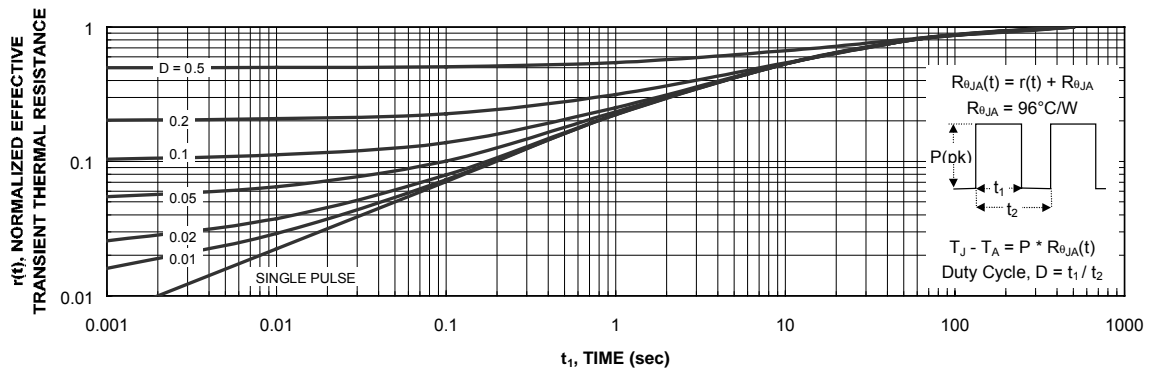


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b. Transient thermal response will change depending on the circuit board design.

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